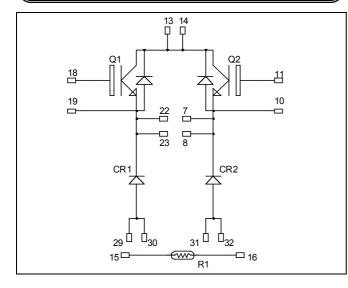
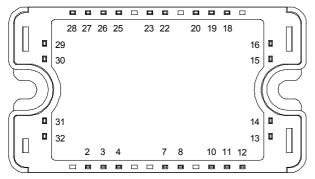


Dual Buck chopper Trench + Field Stop IGBT3 Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

APTGT50DSK60T3G

$V_{CES} = 600V$ $I_{C} = 50A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Symmetrical design
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- Each leg can be easily paralleled to achieve a single buck of twice the current capability.
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
Т	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	50	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V _{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	176	W
RBSOA	Reverse Bias Safe Operating Area	$T_{\rm J} = 150^{\circ}{\rm C}$	100A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_j = 25^{\circ}C$			1.5	1.9	V
V _{CE(sat)}		$I_C = 50A$	$T_{j} = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600 \mu A$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			3150		
C _{oes}	Output Capacitance				200		pF
C _{res}	Reverse Transfer Capacitance				95		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			110		
Tr	Rise Time	$V_{GE} = \pm 15V$			45		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 50A$			200		
T _f	Fall Time	$R_G = 8.2\Omega$			40		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 50A$			120		
T _r	Rise Time				50		ns
T _{d(off)}	Turn-off Delay Time				250		
T _f	Fall Time	$R_G = 8.2\Omega$			60		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 25^{\circ}C$		0.3		mJ
Lon	run-on Switching Ellergy		$T_{j} = 150^{\circ}C$		0.43		1115
E_{off}	Turn-off Switching Energy	$I_{\rm C} = 50A$	$T_j = 25^{\circ}C$		1.35		mJ
		$R_G = 8.2\Omega$	$T_{j} = 150^{\circ}C$		1.75		1115

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$			250	μA
IRM	Maximum Reverse Leakage Current	• _R -000 •	$T_{j} = 150^{\circ}C$			500	μл
I _F	DC Forward Current		$Tc = 80^{\circ}C$		50		А
V _F	Diode Forward Voltage	$I_{\rm F} = 50 A$ $V_{\rm GE} = 0 V$	$T_i = 25^{\circ}C$		1.6	2	V
• F	blode i of ward voltage		$T_{i} = 150^{\circ}C$		1.5		•
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
۹r	Reverse Receivery Time		$T_{j} = 150^{\circ}C$		150		115
0	Q_{rr} Reverse Recovery Charge $I_F = 50A$ $V_R = 300V$ $di/dt = 1800A/\mu s$	$I_F = 50A$ $V_F = 200V$	$T_j = 25^{\circ}C$		2.6		μC
Qrr		$T_{j} = 150^{\circ}C$		5.4		μυ	
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		0.6		mJ
Ľr			$T_{j} = 150^{\circ}C$		1.2		1113



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Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

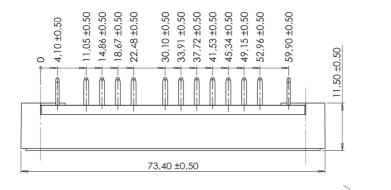
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
-	$R_{-} = \frac{R_{25}}{1}$ T: Thermistor temperature				

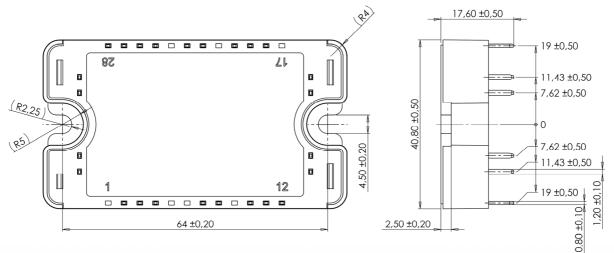
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.85	°C/W
K _{thJC}			Diode			1.42	C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range		-40		175		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

SP3 Package outline (dimensions in mm)



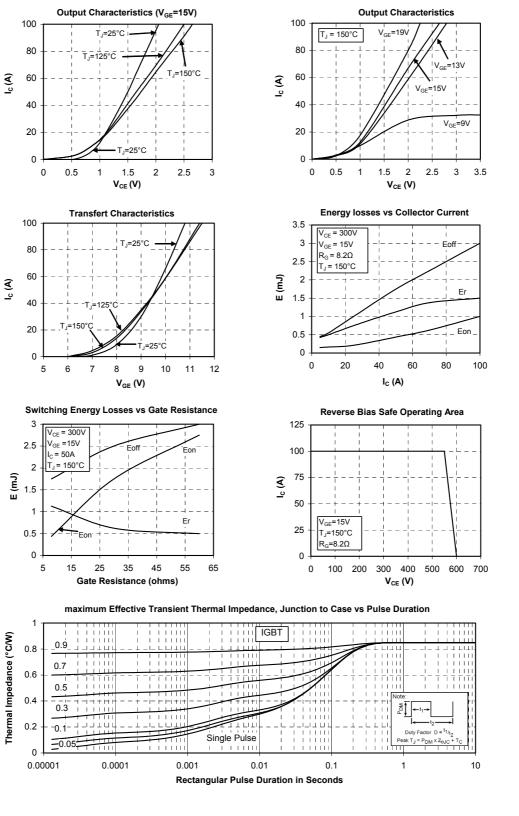


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

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Typical Performance Curve



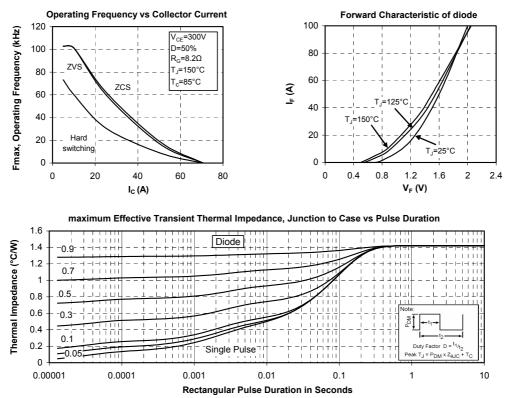
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